

TRANSISTOR (PNP)

FEATURES

Complementary Type The NPN Transistor

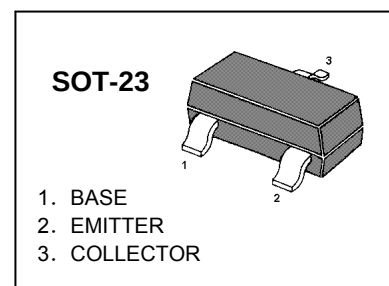
MMBT3904 is Recommended

Epitaxial Planar Die Construction

MARKING: 2A

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-200	mA
P_C	Total Device Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	625	$^{\circ}\text{C}/\text{W}$
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55 ~ +150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-40\text{V}, I_E=0$		-0.1	μA
Collector cut-off current	I_{CEX}	$V_{CE}=-30\text{V}, V_{BE(off)}=-3\text{V}$		-50	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1\text{V}, I_C=-1\text{mA}$	100	300	
	$h_{FE(2)}$	$V_{CE}=-1\text{V}, I_C=-10\text{mA}$	100	300	
	$h_{FE(3)}$	$V_{CE}=-1\text{V}, I_C=-50\text{mA}$	60		
	$h_{FE(4)}$	$V_{CE}=-1\text{V}, I_C=-100\text{mA}$	30		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$		-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$		-0.95	V
Transition frequency	f_T	$V_{CE}=-20\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$	300		MHz
Delay Time	t_d	$V_{CC}=-3\text{V}, V_{BE}=-0.5\text{V}$		35	nS
Rise Time	t_r	$I_C=-10\text{mA}, I_{B1}=-I_{B2}=-1\text{mA}$		35	nS
Storage Time	t_s	$V_{CC}=-3\text{V}, I_C=-10\text{mA},$		225	nS
Fall Time	t_f	$I_{B1}=-I_{B2}=-1\text{mA}$		75	nS

Typical Characteristics

MMBT3906

